

Silicon NPN Power Transistors

2N5468 2N5469

DESCRIPTION

- With TO-66 package
- High-voltage capability
- Fast switching speeds
- Low saturation voltage

APPLICATIONS

- They are intended for use in off-line power supplies ,inverter and converter circuits

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

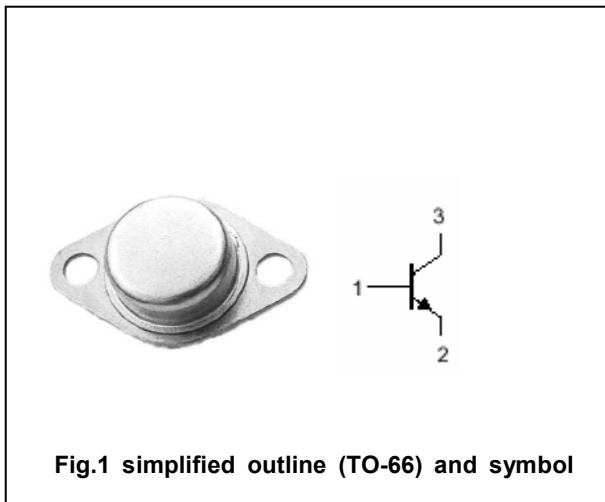


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
V _{CBO}	Collector-base voltage	Open emitter	2N5468	500	V
			2N5469	700	
V _{CEO}	Collector-emitter voltage	Open base	400	V	
V _{EBO}	Emitter-base voltage	Open collector	7	V	
I _C	Collector current		3	A	
I _{CM}	Collector current-peak		5	A	
I _B	Base current		1	A	
P _D	Total Power Dissipation	T _C =25□	70	W	
T _j	Junction temperature		150	□	
T _{stg}	Storage temperature		-65~200	□	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	5.0	□/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A ; I _B =0	400			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A; I _B =0.4A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2A; I _B =0.4A			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =ratedV _{CEO} ; I _E =0			1.0	mA
I _{CEV}	Collector cut-off current	V _{CE} =ratedV _{CEO} ; V _{BE(off)} =1.5V T _C =125°C			1.0 5.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	mA
h _{FE}	DC current gain	I _C =3A ; V _{CE} =5V	15		60	
f _T	Transistion frequency	I _C =1A ; V _{CE} =10V;f=1MHz	2.5			MHz

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PACKAGE OUTLINE

